

Title (en)

An inexpensive method of manufacturing an SOI wafer

Title (de)

Ein preiswertes Verfahren zur Herstellung eines SOI-Wafers

Title (fr)

Procédé économique de fabrication d'une puce SOI

Publication

**EP 0978872 B1 20111012 (EN)**

Application

**EP 98830476 A 19980803**

Priority

EP 98830476 A 19980803

Abstract (en)

[origin: EP0978872A1] The method comprises the following steps: selective anisotropic etching to form, in the substrate (2'), trenches (16) which extend to a predetermined depth from a major surface of the substrate (2') and between which portions (18) of the substrate (2') are defined, selective isotropic etching to enlarge the trenches (16), starting a predetermined distance from the major surface, thus reducing the thicknesses of the portions (18') of the substrate between adjacent trenches (16), selective oxidation to convert the portions (18') of reduced thickness of the substrate (2') into silicon dioxide (22) and to fill the trenches (16) with silicon dioxide, starting substantially from the said predetermined distance, and epitaxial growth of a silicon layer on the major surface of the substrate (2'). The method permits great freedom in the selection of the dimensional ratios between the trenches and the pillars and thus enables the necessary crystallographic quality of the epitaxial layer to be achieved, ensuring a continuous buried oxide layer. <IMAGE> <IMAGE> <IMAGE>

IPC 8 full level

**H01L 21/316** (2006.01); **H01L 21/762** (2006.01); **H01L 27/12** (2006.01)

CPC (source: EP)

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